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N-CHANNEL ENHANCEMENT MODE FIELD MOSFET

Product Summary

V _{SSS}	R _{SS(ON)}	I _S T _A = +25°C
12V	$26m\Omega$ @ V_{GS} = $4.5V$	5.5 A

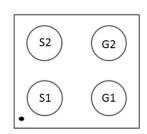
Description

This new generation MOSFET has been designed to minimize the onstate resistance (R_{SS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Battery Management
- Load Switch
- Battery Protection





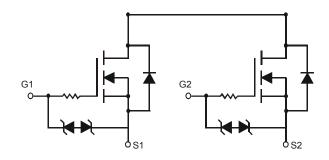
Top View

Features and Benefits

- Built-in G-S protection diode against ESD 2kV HBM.
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- · Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: U-WLB1818-4
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Weight: 0.005 grams (approximate)



Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging		
DMN1033UCB4-7	U-WLB1818-4	3000/Tape & Reel		

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



GW = Product Type Marking Code YM = Date Code Marking Y = Year (ex: Y = 2011) M = Month (ex: 9 = September)

Date Code Key

Date Code Ito,		_		_		_	_				_	
Year	200	9	2010		2011	20)12	2013		2014	2	2015
Code	W		Χ		Υ		Z	Α		В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings

Charac	teristic		Symbol	Value	Units
Drain-Source Voltage			V _{SSS}	12	V
Gate-Source Voltage			V _{GSS}	±6	V
Continuous Source Current @ V _{GS} = 4.5V T _A = +25°C (Note 5)	9 ' ''			5.5 4.5	А
Pulsed Source Current @ T _A = +25°C (Notes 5 & 6)			I _{SM}	20	A

Thermal Characteristics

Characteristic	Symbol	Value	Units
Power Dissipation, @T _A = +25°C (Note 5)	P_{D}	1.45	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 5)	$R_{ hetaJA}$	88.21	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

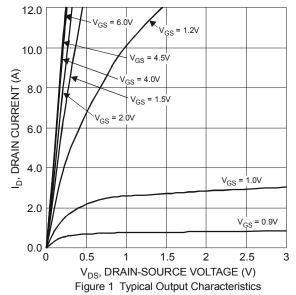
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Source to Source Breakdown Voltage T _J = +25°C	V _{(BR)SS}	12	_	_	V	$I_S = 1$ mA, $V_{GS} = 0$ V	
Zero Gate Voltage Source Current T _J = +25°C	I _{SSS}	_	_	1.0	μA	V _{SS} = 12V, V _{GS} = 0V	
Gate-Body Leakage	I _{GSS}	_	_	±10	μA	$V_{GS} = \pm 6V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(th)}	0.35	0.5	0.7	V	V _{SS} = 10V, I _S = 1.0mA	
			19.5	26		V _{GS} = 4.5V, I _S = 3.0A	
			20	27		$V_{GS} = 4.0V, I_{S} = 3.0A$	
	Rss(on)		20.5	28		$V_{GS} = 3.7V, I_S = 3.0A$	
Static Source -Source On-Resistance			21	29	mΩ	$V_{GS} = 3.5V$, $I_{S} = 3.0A$	
Static Source -Source Off-Resistance		_	21.5	30	11152	$V_{GS} = 3.1V$, $I_{S} = 3.0A$	
			22	31		$V_{GS} = 2.5V, I_S = 3.0A$	
			26	33		$V_{GS} = 1.8V, I_S = 3.0A$	
			35	50		$V_{GS} = 1.5V, I_S = 3.0A$	
Forward Transfer Admittance	Y _{fs}	_	11	-	S	V _{SS} = 10V, I _S = 3.0A	
Body Diode Forward Voltage	V _{F(S-S)}	_	0.7	1.0	V	I _F = 3.0 A, V _{GS} = 0 V,	
DYNAMIC CHARACTERISTICS (Note 8)							
Total Gate Charge	Qg	_	37	_	nC	$V_{GS} = 4.5V, V_{SS} = 10V, I_{S} = 6A$	
Turn-On Delay Time	t _{D(on)}	_	10	_	ns		
Turn-On Rise Time	t _r	1	20	-	ns	V _{DD} = 6V,	
Turn-Off Delay Time	t _{D(off)}	_	83	_	ns	$R_L = 6.0\Omega$, $I_S = 3.0A$	
Turn-Off Fall Time	t _f	_	52	_	ns]	

Notes:

- Device mounted on FR4 material with 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu.
 Repetitive rating, pulse width limited by junction temperature.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to production testing.





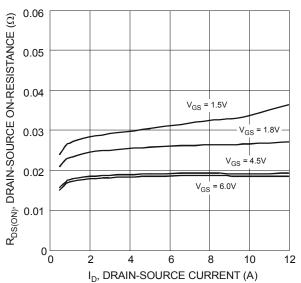
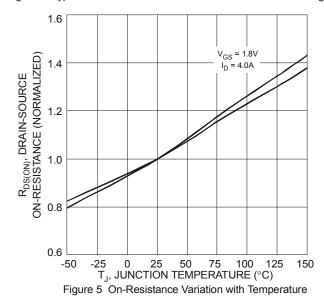
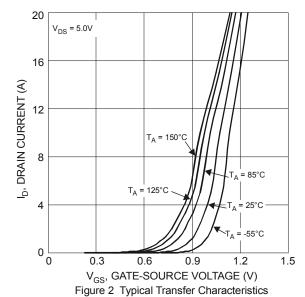


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage





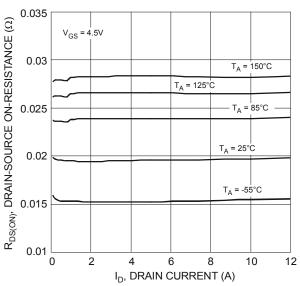


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

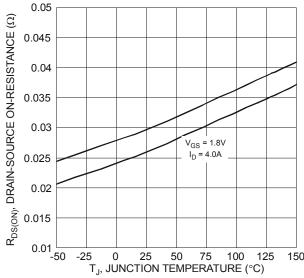


Figure 6 On-Resistance Variation with Temperature



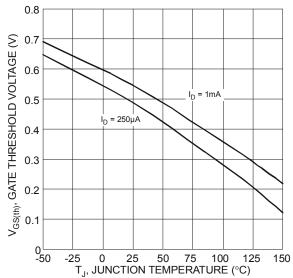
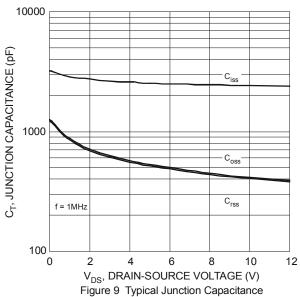


Figure 7 Gate Threshold Variation vs. Ambient Temperature



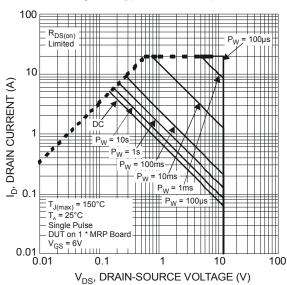
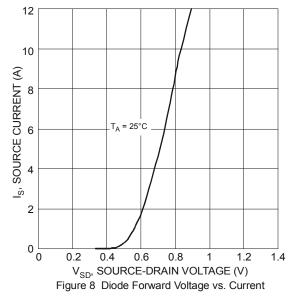


Figure 11 SOA, Safe Operation Area



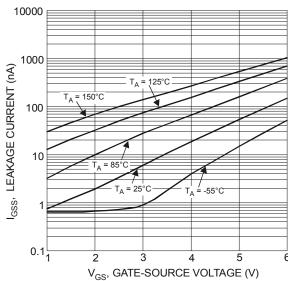
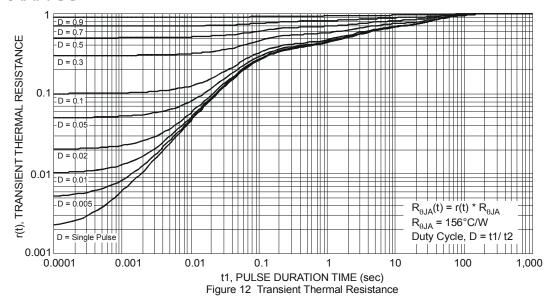


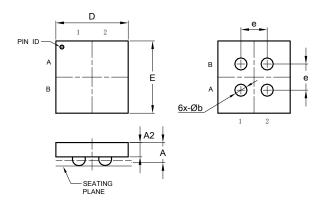
Figure 10 Gate-Source Leakage Current vs. Voltage





Package Outline Dimensions

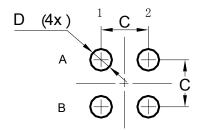
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



U-WLB1818-4							
Dim	Min	Max	Тур				
Α	_	0.62	_				
A2	-	-	0.36				
b	0.25	0.35	0.30				
D	1.75	1.80	1.79				
Е	1.75	1.80	1.79				
е	_	_	0.65				
All Dimensions in mm							

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
C	0.65
D	0.30



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